

Serial No. 09/611,955

Art Unit: 2811

IN THE SPECIFICATION

Please replace the paragraph beginning at page 7, line 16, with the following rewritten paragraph:

D2
In accordance with the present invention, recesses 2 such as troughs and vias are provided in at least one major surface of a semiconductor substrate 13. Typical semiconductor substrates include silicon and group III-V semiconductors. Electrical insulation 3 is provided over the major surface and in the recesses such as silicon dioxide which can be thermally grown or deposited such as by chemical vapor deposition or physical vapor deposition. Typically, the insulating layer is about 2000 to about 30,000 Å thick, and more typically about 4000 to about 20,000 Å thick.

Please replace the paragraph beginning at page 13, line 1, with the following rewritten paragraph:

D3
According to an alternative process according to the present invention, recesses 2 such as troughs and vias are provided in at least one major surface of a semiconductor substrate 13. Electrical insulation 3 is provided over the major surface and in the recesses such as silicon dioxide which can be thermally grown or deposited such as by chemical vapor deposition or physical vapor deposition. Typically, the insulating layer is about 2000 to about 30,000 Å thick, and more typically about 4000 to about 20,000 Å thick.